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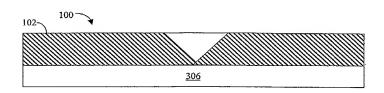
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(54) Title: CONTROLLING REMOVAL RATE UNIFORMITY OF AN ELECTROPOLISHING PROCESS IN INTEGRATED CIRCUIT FABRICATION



(57) Abstract: A metal layer formed on a wafer, the wafer having a center portion and an edge portion, is electropolished by aligning a nozzle and the wafer to position the nozzle adjacent to the center portion of the wafer. The wafer is rotated. As the wafer is rotated, a stream of electrolyte is applied from the nozzle onto a portion of the metal layer adjacent to the center portion of the wafer to begin to electropolish the portion of the metal layer with a triangular polishing profile to initially expose an underlying layer underneath the metal layer at a point.



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